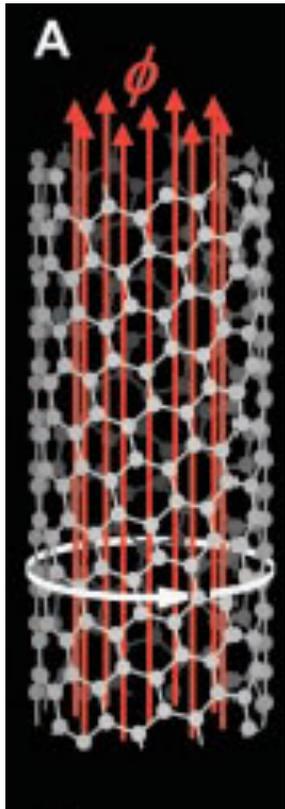


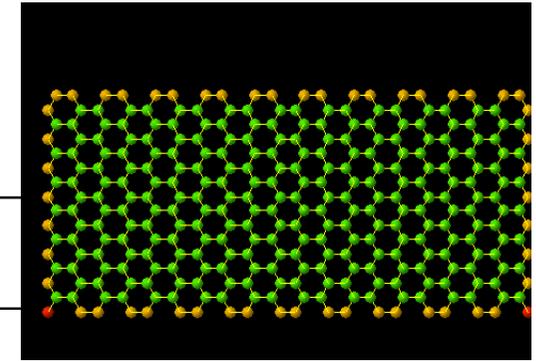
Aharonov–Bohm Effects and Conductivity in Carbon Nanotubes

Takeshi Nakanishi (AIST,ISSP,CREST) and
Tsuneya Ando (TIT)

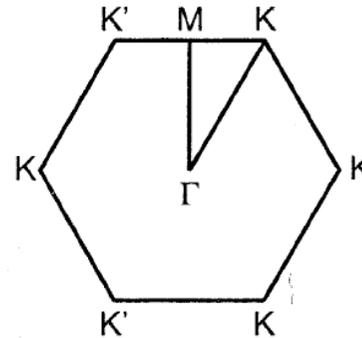
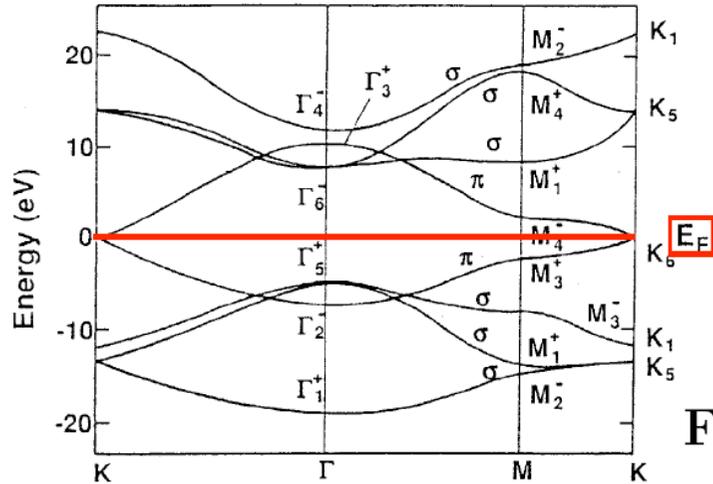


- Introduction
 - AB effect
 - Absence of back scattering
 - Effective flux for strain, curvature and stress effects
- Boltzmann conductivity in carbon nanotubes with magnetic flux in axis direction
- Impurity and electron–phonon scatterings

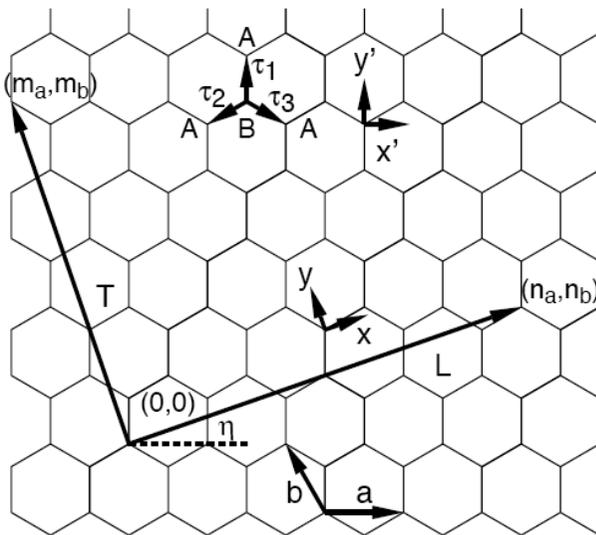
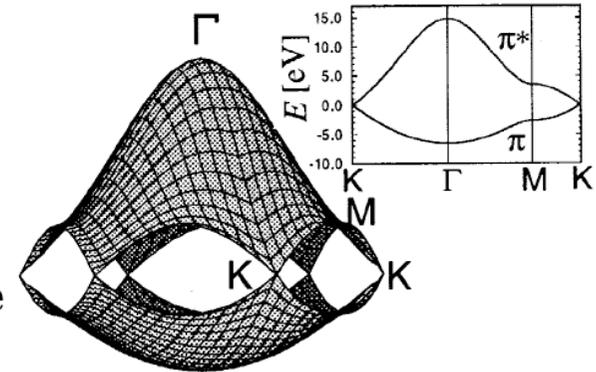
Graphite sheet (Graphene)



S. Maruyama, Univ. Tokyo (Animation)



First Brillouin Zone



sp^2 covalent bonding
single π band

tight-binding model

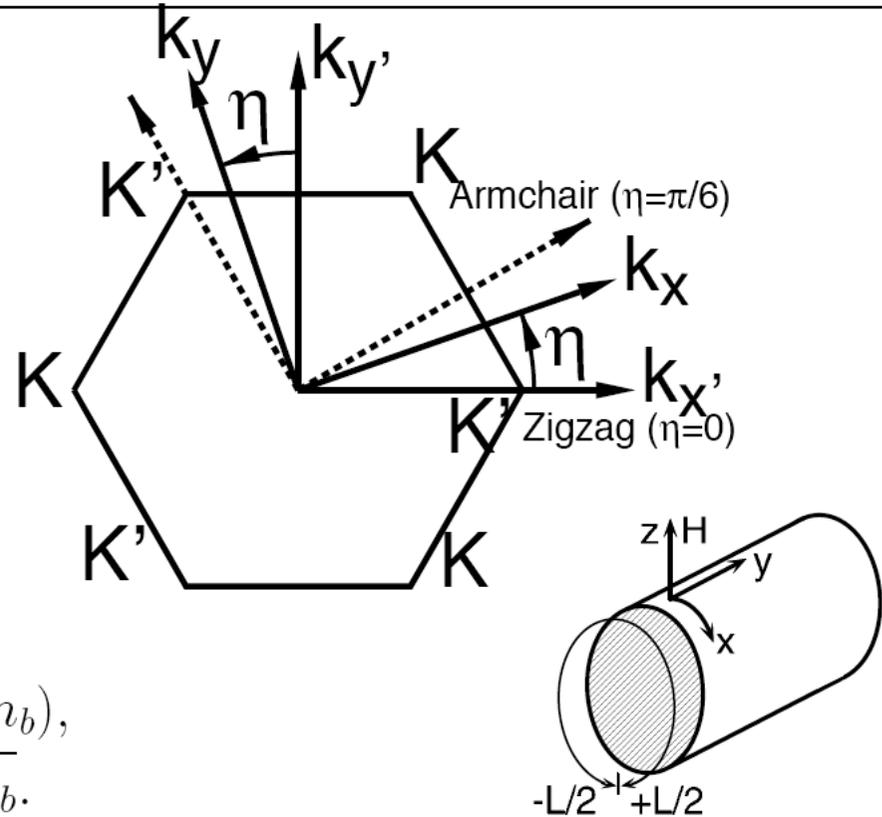
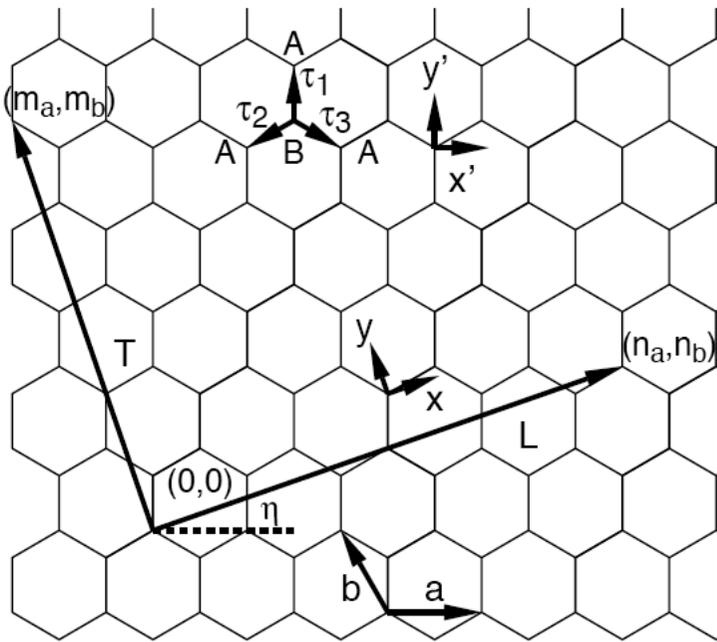
Nearest-neighbor

Transfer Integral: γ_0

$$-\gamma_0 \sum_{l=1}^3 \psi_B(\mathbf{R}_A - \vec{\tau}_l) = \varepsilon \psi_A(\mathbf{R}_A),$$

$$-\gamma_0 \sum_{l=1}^3 \psi_A(\mathbf{R}_B + \vec{\tau}_l) = \varepsilon \psi_B(\mathbf{R}_B).$$

Graphite and Chiral Vector



Chiral Vector: $\mathbf{L} = n_a \mathbf{a} + n_b \mathbf{b} \equiv (n_a, n_b)$,
 $L = |\mathbf{L}| = a\sqrt{n_a^2 + n_b^2 - n_a n_b}$.

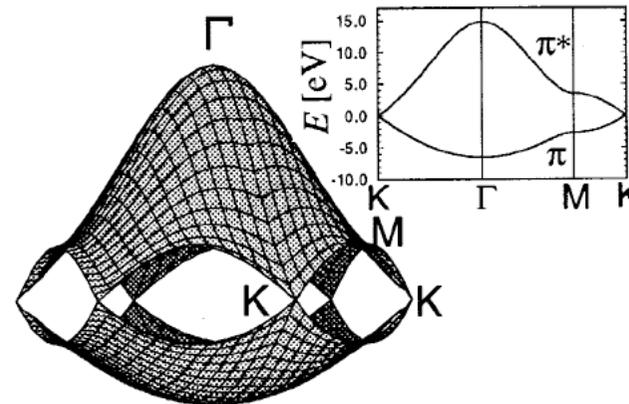
$(n_a, n_b) = (2, 1)m$: **armchair CN**

$(n_a, n_b) = (1, 0)m$: **zigzag CN**

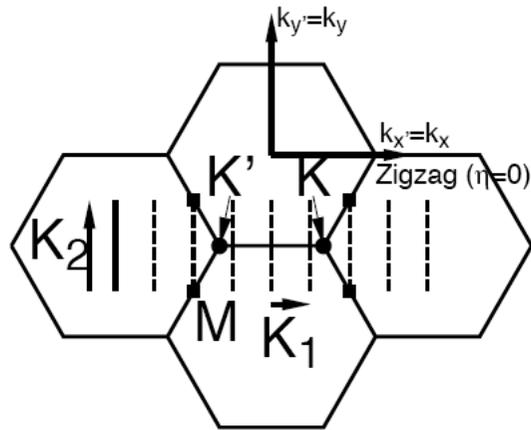
$$n_a + n_b = 3N + \nu$$

$\nu = 0$ **metallic CN**

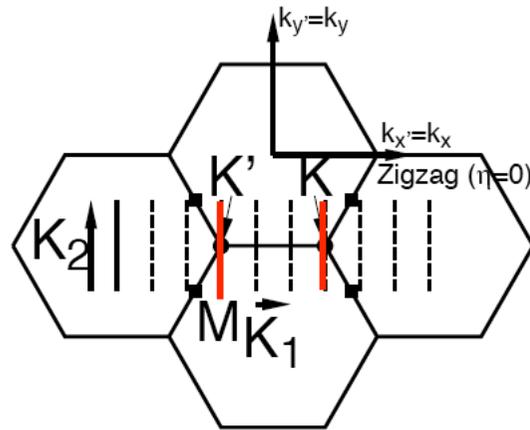
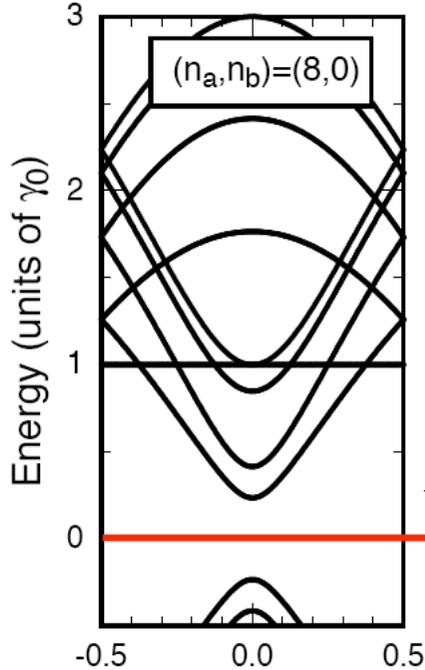
$\nu = \pm 1$ **semiconducting CN**



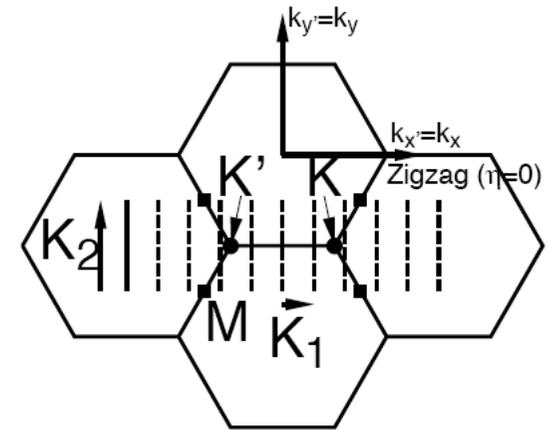
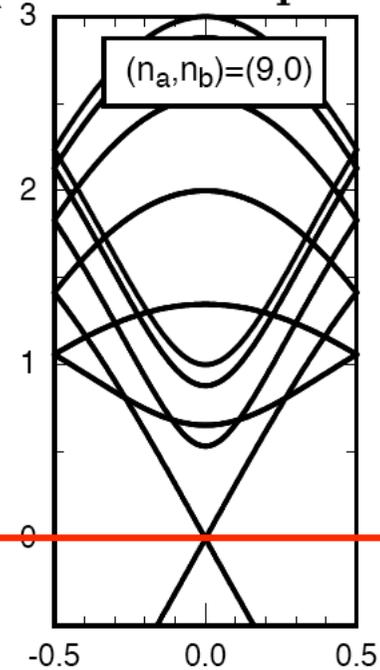
Metallic and Semiconducting CN (Zigzag CN)



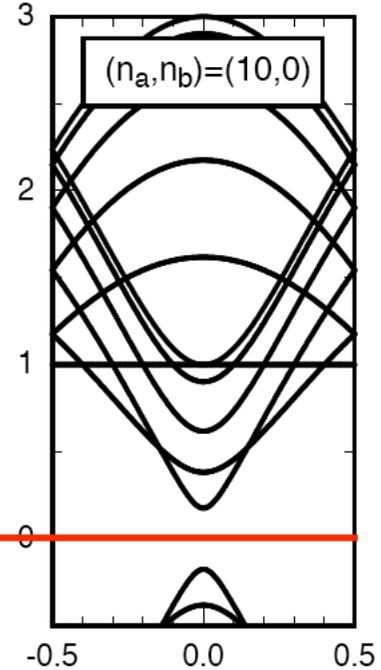
Semiconductor



Metal (Linear dispersion)



Semiconductor



Wave Vector (units of $2\pi/\sqrt{3}a$)

Aharonov–Bohm (AB) effect

H. Ajiki and T. Ando, JPSJ 62 (1993) 1255.

$$\kappa_{\nu,\phi}(n) = \frac{2\pi}{L}(n - \nu/3 + \varphi)$$

$$\varphi = \phi / \phi_0$$

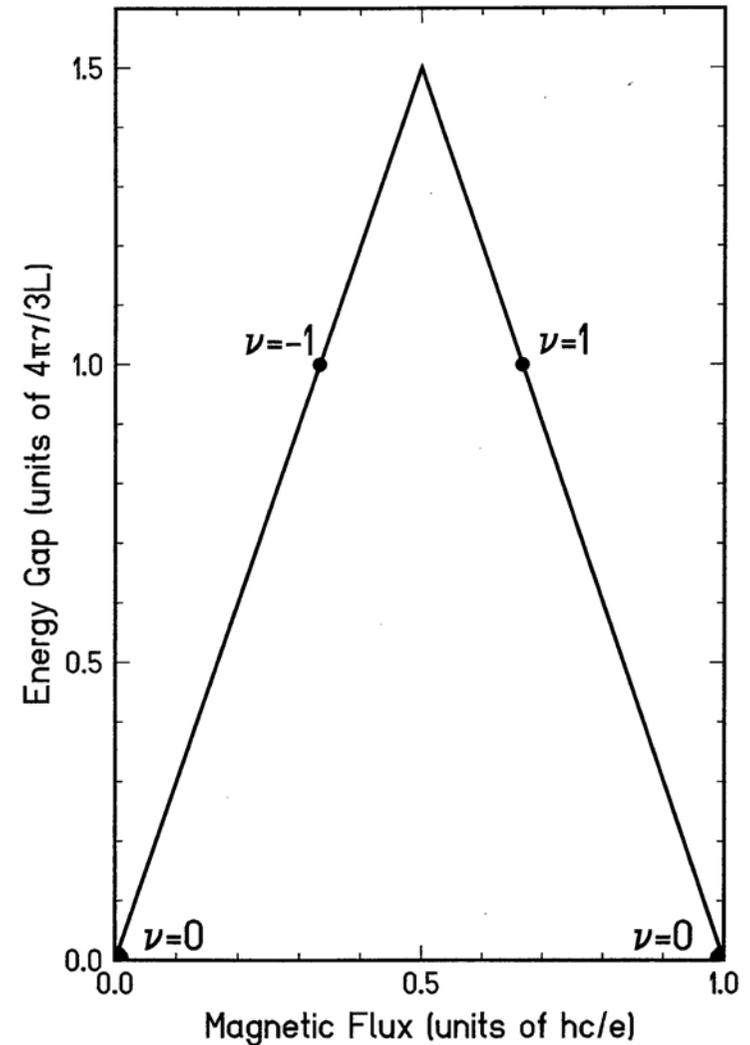
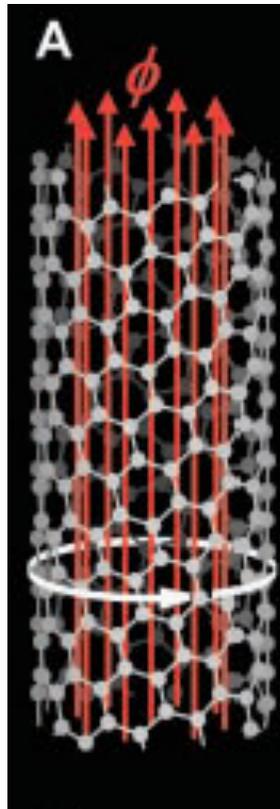
$$\phi_0 = ch / e$$

Energy Gap

$$E_g = \gamma \left| \kappa_{\nu,\phi}(n) \right|$$

5300T (d=1nm)

S.Zaric *et al.* Science 304, 1129 (2004)



Effective–Potential

T. Ando and T. Nakanishi, J. Phys. Soc. Jpn. **67**,1704 (1998)

Effective–Mass Equation

$$(\mathcal{H}_0 + V)\mathcal{F} = \varepsilon\mathcal{F}$$

$$\mathcal{H}_0 = \begin{pmatrix} 0 & \gamma(\hat{k}_x - i\hat{k}_y) & 0 & 0 \\ \gamma(\hat{k}_x + i\hat{k}_y) & 0 & 0 & 0 \\ 0 & 0 & 0 & \gamma(\hat{k}_x + i\hat{k}_y) \\ 0 & 0 & \gamma(\hat{k}_x - i\hat{k}_y) & 0 \end{pmatrix}, \mathcal{F} = \begin{pmatrix} F_A^K(\mathbf{r}) \\ F_B^K(\mathbf{r}) \\ F_A^{K'}(\mathbf{r}) \\ F_B^{K'}(\mathbf{r}) \end{pmatrix}$$

$$V = \begin{pmatrix} u_A(\mathbf{r}) & 0 & e^{i\eta}u'_A(\mathbf{r}) & 0 \\ 0 & u_B(\mathbf{r}) & 0 & -\omega^{-1}e^{-i\eta}u'_B(\mathbf{r}) \\ e^{-i\eta}u'_A(\mathbf{r})^* & 0 & u_A(\mathbf{r}) & 0 \\ 0 & -\omega e^{i\eta}u'_B(\mathbf{r})^* & 0 & u_B(\mathbf{r}) \end{pmatrix}$$

$$u_A = \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_A} \tilde{u}_A(\mathbf{R}_A),$$

$$u_B = \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_B} \tilde{u}_B(\mathbf{R}_B),$$

$$u'_A = \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_A} e^{i(\mathbf{K}'-\mathbf{K})\cdot\mathbf{R}_A} \tilde{u}_A(\mathbf{R}_A),$$

$$u'_B = \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_B} e^{i(\mathbf{K}'-\mathbf{K})\cdot\mathbf{R}_B} \tilde{u}_B(\mathbf{R}_B),$$

$\sqrt{3}a^2/2$: Area of a Unit Cell

Slowly-varying Potential

Potential Range $d \gg a$

$$u_A(\mathbf{r}) = u_B(\mathbf{r})$$

$$u'_A(\mathbf{r}) = u'_B(\mathbf{r}) = 0$$

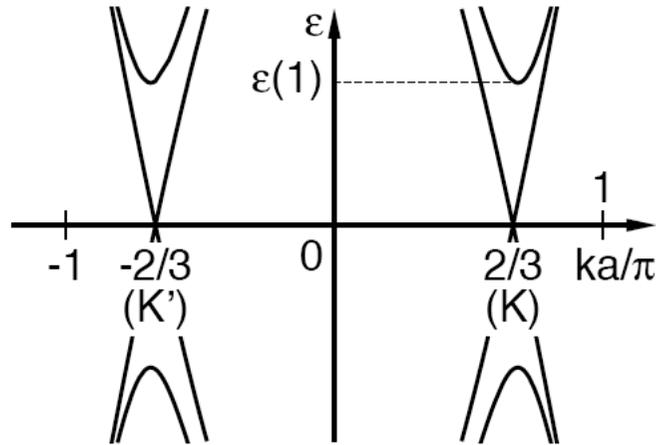
Potential Range $d \ll$ Circumference $L = |\mathbf{L}|$

$$u_A(\mathbf{r}) = u_A\delta(\mathbf{r}-\mathbf{r}_0), \quad u_B(\mathbf{r}) = u_B\delta(\mathbf{r}-\mathbf{r}_0),$$

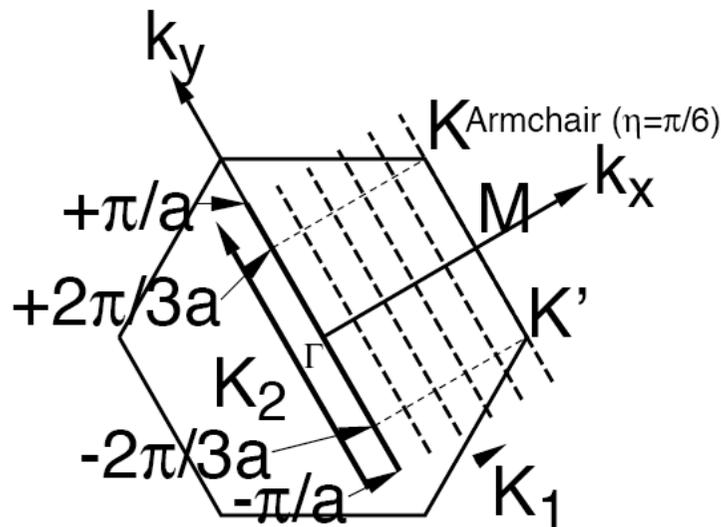
$$u'_A(\mathbf{r}) = u'_A\delta(\mathbf{r}-\mathbf{r}_0), \quad u'_B(\mathbf{r}) = u'_B\delta(\mathbf{r}-\mathbf{r}_0).$$

\mathbf{r}_0 : Impurity Position

Right- and left-going channels



Metallic CN



$(n_a, n_b) = (2, 1)m$
armchair CN

○ Solutions for $V = 0, |\varepsilon| < \varepsilon(1) = \frac{2\pi\gamma}{L}$

$$\mathbf{F}^{K\pm} = \begin{pmatrix} F_A^K(\mathbf{r}) \\ F_B^K(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2AL}} \begin{pmatrix} \mp i \\ 1 \end{pmatrix} \exp(iky),$$

$$\mathbf{F}^{K'\pm} = \begin{pmatrix} F_A^{K'}(\mathbf{r}) \\ F_B^{K'}(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2AL}} \begin{pmatrix} \pm i \\ 1 \end{pmatrix} \exp(iky).$$

A: Length of Nanotube

Energy: $\varepsilon(k) = \pm\gamma k$

Group Velocity: $v = \pm\gamma/\hbar$

$$\pm \begin{cases} \text{Right-going } \mathbf{F}^{K+}, \mathbf{F}^{K'+} \\ \text{Left-going } \mathbf{F}^{K-}, \mathbf{F}^{K'-} \end{cases}$$

Lowest Born Approximation

○ Inter-valley Scattering

$$\begin{aligned}
 V_{K\pm K'+} &= \frac{1}{2AL} \int d\mathbf{r} \begin{pmatrix} \pm i & 1 \\ 0 & 0 \end{pmatrix} \begin{pmatrix} e^{i\eta} u'_A(\mathbf{r}) & 0 \\ 0 & -\omega^{-1} e^{-i\eta} u'_B(\mathbf{r}) \end{pmatrix} \begin{pmatrix} i \\ 1 \end{pmatrix} \\
 &= \frac{1}{2AL} \int d\mathbf{r} \{ \mp e^{i\eta} u'_A(\mathbf{r}) - \omega^{-1} e^{-i\eta} u'_B(\mathbf{r}) \} \\
 &= \frac{1}{2AL} (\mp u'_A e^{i\eta} - \omega^{-1} e^{-i\eta} u'_B) = V_{K'\pm K+}^*
 \end{aligned}$$

○ Intra-valley Scattering

$$\begin{aligned}
 V_{K\pm K+} &= \frac{1}{2AL} \int d\mathbf{r} \begin{pmatrix} \pm i & 1 \\ 0 & 0 \end{pmatrix} \begin{pmatrix} u_A(\mathbf{r}) & 0 \\ 0 & u_B(\mathbf{r}) \end{pmatrix} \begin{pmatrix} -i \\ 1 \end{pmatrix} \\
 &= \frac{1}{2AL} \int d\mathbf{r} \{ \pm u_A(\mathbf{r}) + u_B(\mathbf{r}) \} \\
 &= \frac{1}{2AL} (\pm u_A + u_B) = V_{K'\pm K'+}
 \end{aligned}$$

Absence of back-scattering for slowly varying potential

$$V_{K-K'+} = V_{K'-K+}^* = 0, \quad V_{K-K+} = V_{K'-K'+} \propto u_B - u_A = 0$$

Absence of Back Scattering ($d \gg a$)

$$T = V + V \frac{1}{\varepsilon - \mathcal{H}_0} V + V \frac{1}{\varepsilon - \mathcal{H}_0} V \frac{1}{\varepsilon - \mathcal{H}_0} V + \dots$$

$$\mathcal{H}_0 = \gamma \begin{pmatrix} 0 & \hat{k}_x - i\hat{k}_y \\ \hat{k}_x + i\hat{k}_y & 0 \end{pmatrix}$$

Long range Potential

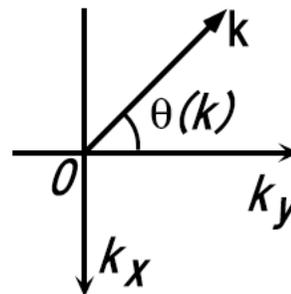
$$V = \begin{pmatrix} V(\mathbf{r}) & 0 \\ 0 & V(\mathbf{r}) \end{pmatrix}$$

$$\mathbf{F}_{s\mathbf{k}}(\mathbf{r}) = \frac{1}{\sqrt{LA}} \exp(i\mathbf{k} \cdot \mathbf{r}) \mathbf{F}_{s\mathbf{k}},$$

$$\varepsilon_s(\mathbf{k}) = s\gamma|\mathbf{k}|,$$

$s = +1$ **conduction band**

$s = -1$ **valence band**



$$\varepsilon_s(-\mathbf{k}) = \varepsilon_s(\mathbf{k})$$

$$\mathbf{F}_{s\mathbf{k}} = \exp[i\phi_s(\mathbf{k})] R^{-1}[\theta(\mathbf{k})] |s\rangle,$$

$$k_x + ik_y = i|\mathbf{k}|e^{i\theta(\mathbf{k})}$$

Spin-rotation operator

$$R(\theta) = \exp\left(i\frac{\theta}{2}\sigma_z\right)$$

$$= \begin{pmatrix} \exp(+i\theta/2) & 0 \\ 0 & \exp(-i\theta/2) \end{pmatrix}$$

$$|s\rangle = \frac{1}{\sqrt{2}} \begin{pmatrix} -is \\ 1 \end{pmatrix}$$

Absence of Back Scattering ($d \gg a$)

T. Ando and T. Nakanishi, J. Phys. Soc. Jpn. **67**,1704 (1998)

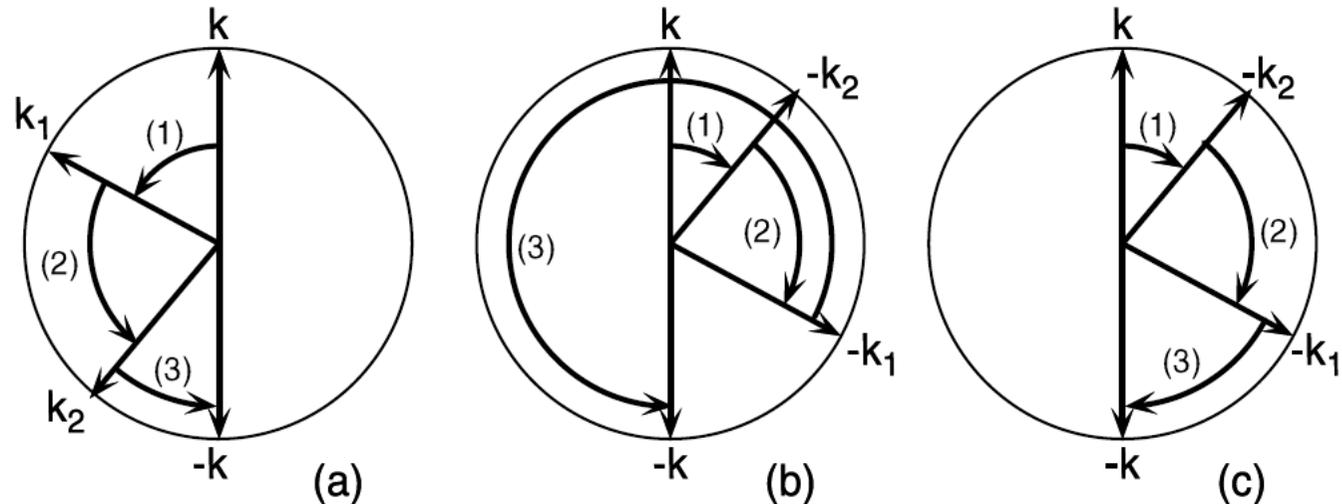
$(p+1)$ th order term

$$\begin{aligned}
 (s, -\mathbf{k} | T^{(p+1)} | s, +\mathbf{k}) &= \frac{1}{LA} \sum_{s_1 \mathbf{k}_1} \frac{1}{LA} \sum_{s_2 \mathbf{k}_2} \cdots \frac{1}{LA} \sum_{s_p \mathbf{k}_p} \\
 &\times \frac{V(-\mathbf{k} - \mathbf{k}_p) \cdots V(\mathbf{k}_2 - \mathbf{k}_1) V(\mathbf{k}_1 - \mathbf{k})}{[\varepsilon - \varepsilon_{s_p}(\mathbf{k}_p)] \cdots [\varepsilon - \varepsilon_{s_2}(\mathbf{k}_2)] [\varepsilon - \varepsilon_{s_1}(\mathbf{k}_1)]} \\
 &\times e^{-i\phi_s(-\mathbf{k})} (s | R[\theta(-\mathbf{k})] R^{-1}[\theta(\mathbf{k}_p)] | s_p) \\
 &\times \cdots \times (s_2 | R[\theta(\mathbf{k}_2)] R^{-1}[\theta(\mathbf{k}_1)] | s_1) \\
 &\times (s_1 | R[\theta(\mathbf{k}_1)] R^{-1}[\theta(\mathbf{k})] | s) e^{i\phi_s(\mathbf{k})}
 \end{aligned}$$

time-reversal terms
cancel out

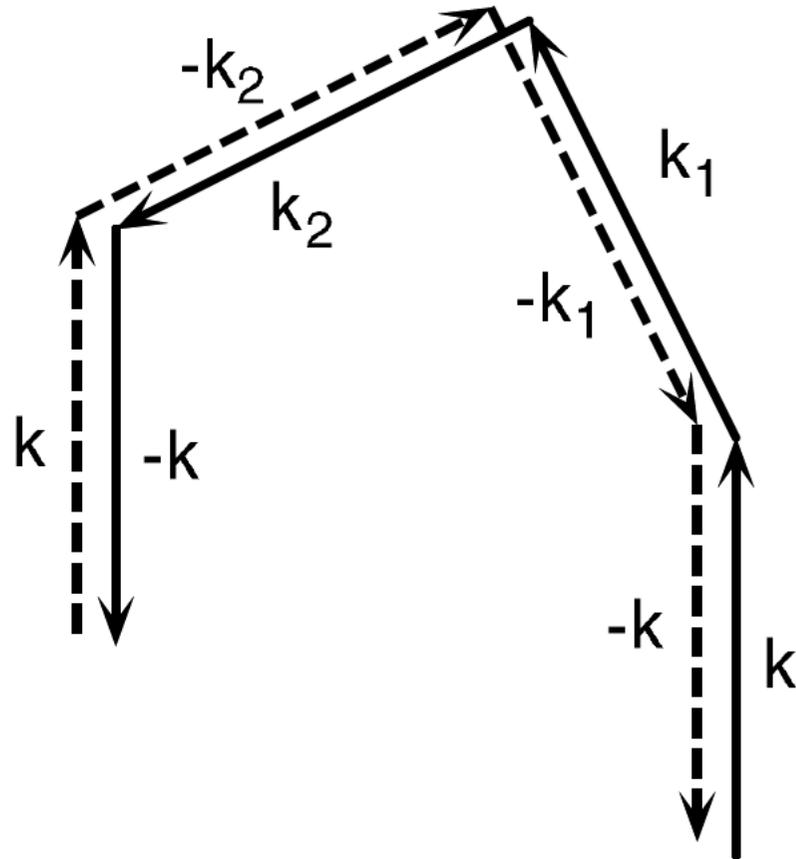
$$\begin{aligned}
 (s_1, k_1) &\rightarrow (s_p, -k_p), \\
 (s_2, k_2) &\rightarrow (s_{p-1}, -k_{p-1}), \dots \\
 R[\theta] &= -R[\theta + 2\pi]
 \end{aligned}$$

$$\varepsilon_s(-\mathbf{k}) = \varepsilon_s(\mathbf{k})$$



Berry's Phase and Absence of Back Scattering

T. Ando, T. Nakanishi, and R. Saito, J. Phys. Soc. Jpn. **67**,2857 (1998)



$$\psi_s(\mathbf{k}) = \frac{1}{\sqrt{2}} \begin{pmatrix} -is \\ \exp[i\theta(\mathbf{k})] \end{pmatrix}$$

$$\psi_s(\mathbf{k}) \longrightarrow \psi_s(\mathbf{k}) \exp(-i\varphi)$$

Berry's Phase

$$\varphi = -i \int_0^T dt \langle \psi_s[\mathbf{k}(t)] | \frac{d}{dt} \psi_s[\mathbf{k}(t)] \rangle = \pi$$

$$R[\theta - 2\pi] = -R[\theta]$$

$$R[-\pi] = -R[\pi]$$

Impurity Scattering

➤ **Absence of back scattering**

T. Ando and TN, JPSJ 67 (1998) 1704

➤ Long-range potential

Diagonal effective potential

➤ **Linear band** in Metallic CN

➤ **Short-range potential**

Off-diagonal effective potential

➤ **δ** : short-range/long-range

$$V_L(\mathbf{r}) \begin{matrix} & \mathbf{KA} & \mathbf{KB} & \mathbf{K'A} & \mathbf{K'B} \\ \left(\begin{array}{cccc} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 1 & 0 \\ 0 & 0 & 0 & 1 \end{array} \right) \end{matrix}$$

$$V_S^A(\mathbf{r}) \begin{matrix} & & & & \\ \left(\begin{array}{cccc} 1 & 0 & e^{i\phi} & 0 \\ 0 & 0 & 0 & 0 \\ e^{-i\phi} & 0 & 1 & 0 \\ 0 & 0 & 0 & 0 \end{array} \right) & & & & \end{matrix}$$

$$\phi = (\mathbf{K}' - \mathbf{K})\mathbf{R}_i^A - \eta$$

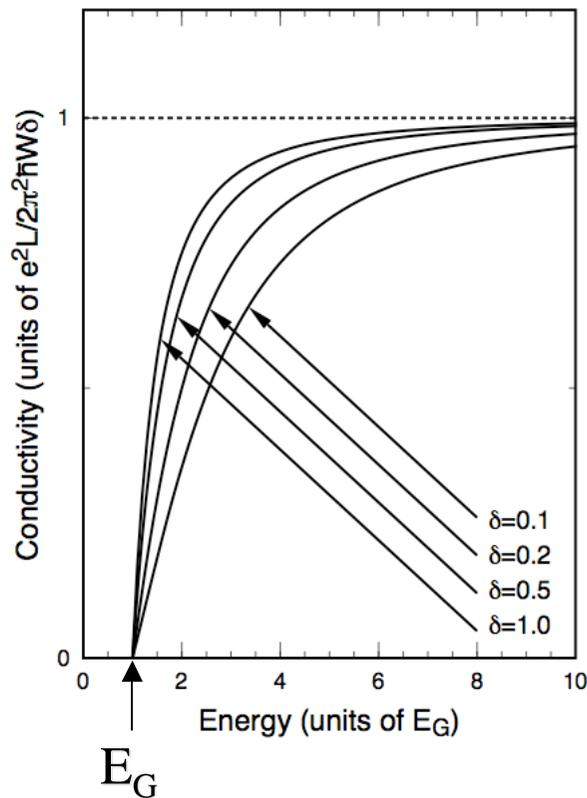
Boltzmann Conductivity

Metallic Nanotube

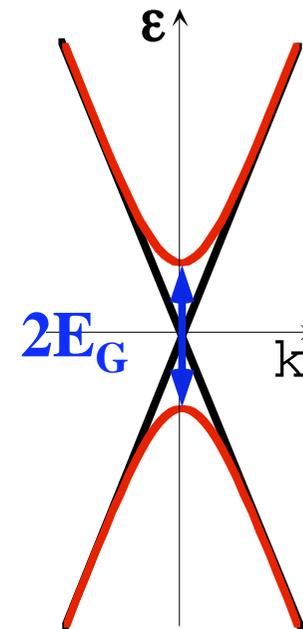
$$\sigma(\varepsilon) = \frac{e^2 L}{\pi^2 \hbar W} \frac{1}{2\delta}$$

Perfect Conductor w/o short-range potential
(δ : ratio of short-range potential)

Non-Metallic Nanotube



Nanotubes with
Energy Gap E_G
(2 Bands)



Strain (stretch, stress, etc) effects

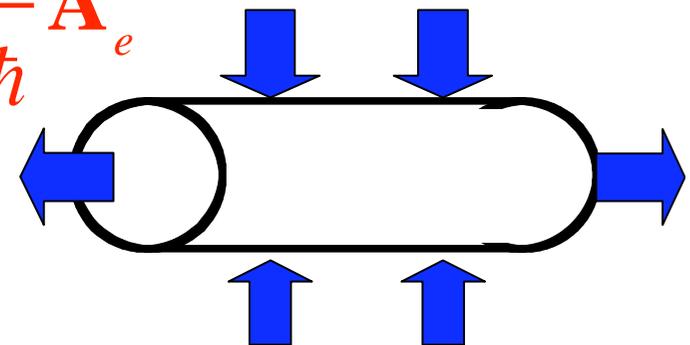
$$H_K = \gamma \begin{pmatrix} 0 & \hat{k}_x - i\hat{k}_y \\ \hat{k}_x + i\hat{k}_y & 0 \end{pmatrix} + \begin{pmatrix} V_1 & V_2 \\ V_2^* & V_1 \end{pmatrix}$$

$$H_{K'} = \gamma \begin{pmatrix} 0 & \hat{k}_x + i\hat{k}_y \\ \hat{k}_x - i\hat{k}_y & 0 \end{pmatrix} + \begin{pmatrix} V_1 & -V_2^* \\ -V_2 & V_1 \end{pmatrix}$$

$$V_2 = g_2 e^{3i\eta} (u_{xx} - u_{yy} + 2iu_{xy})$$

$$\hat{\mathbf{k}} = -i\vec{\nabla} + \frac{e}{c\hbar} \mathbf{A} \rightarrow -i\vec{\nabla} + \frac{e}{c\hbar} \mathbf{A} + \frac{e}{c\hbar} \mathbf{A}_e$$

$$\mathbf{A}_e = \frac{c\hbar}{e} \Re V_2 / \gamma$$



Suzuura and Ando,
PRB 65 (2002) 235412

Effective flux of strain effect

$$\frac{\phi}{\phi_0} = \frac{1}{2\pi\gamma} \int_c \Re V_2 dx$$

$$= \frac{Lg_2}{2\pi\gamma} \left[(u_{xx} - u_{yy}) \cos 3\eta - 2u_{xy} \sin 3\eta \right]$$

stretch,

twisting

breathing(stress)

$$(u_x \neq 0, u_y = u_z = 0)$$

➤ Zigzag($\eta=0$)

Stretch, Breathing(stress)

➤ Armchair($\eta=\pi/6$)

Twist

$$\mathbf{u}(\mathbf{r}) = \mathbf{u}_{nq} \exp[i\chi(n)x + iqy]$$

$$\chi(n) = 2\pi n / L$$

$$n=0$$

T.Ando: JPSJ 73 (2004)3351

Effective flux of curvature effect

T. Ando: JPSJ **69** (2000)1757; **74** (2005) 777

π, σ mixing

max. in Zigzag($\eta=0$), not in Armchair ($\eta=\pi/6$)

$$\frac{\phi}{\phi_0} = -\frac{2\pi}{4\sqrt{3}} \frac{a}{L} p \cos 3\eta \quad (\text{K point}) \quad -\phi \quad (\text{K' point})$$

$$p = 1 - \frac{3\gamma'}{8\gamma} \quad \gamma' = -\frac{\sqrt{3}}{2} V_{pp}^{\pi} a \quad V_{pp}^{\pi} = -\gamma_0$$

$$|p| < 1 \quad \gamma = -\frac{\sqrt{3}}{2} (V_{pp}^{\sigma} - V_{pp}^{\pi}) a$$

$$\phi / \phi_0 \sim 0.05 p \cos 3\eta \quad (L \sim 5\text{nm})$$

$$\Delta k_y = -\frac{\pi^2}{4\sqrt{3}} \frac{a}{L^2} \left(\frac{5\gamma'}{8\gamma} - 1 \right) \sin 3\eta$$

Effective flux

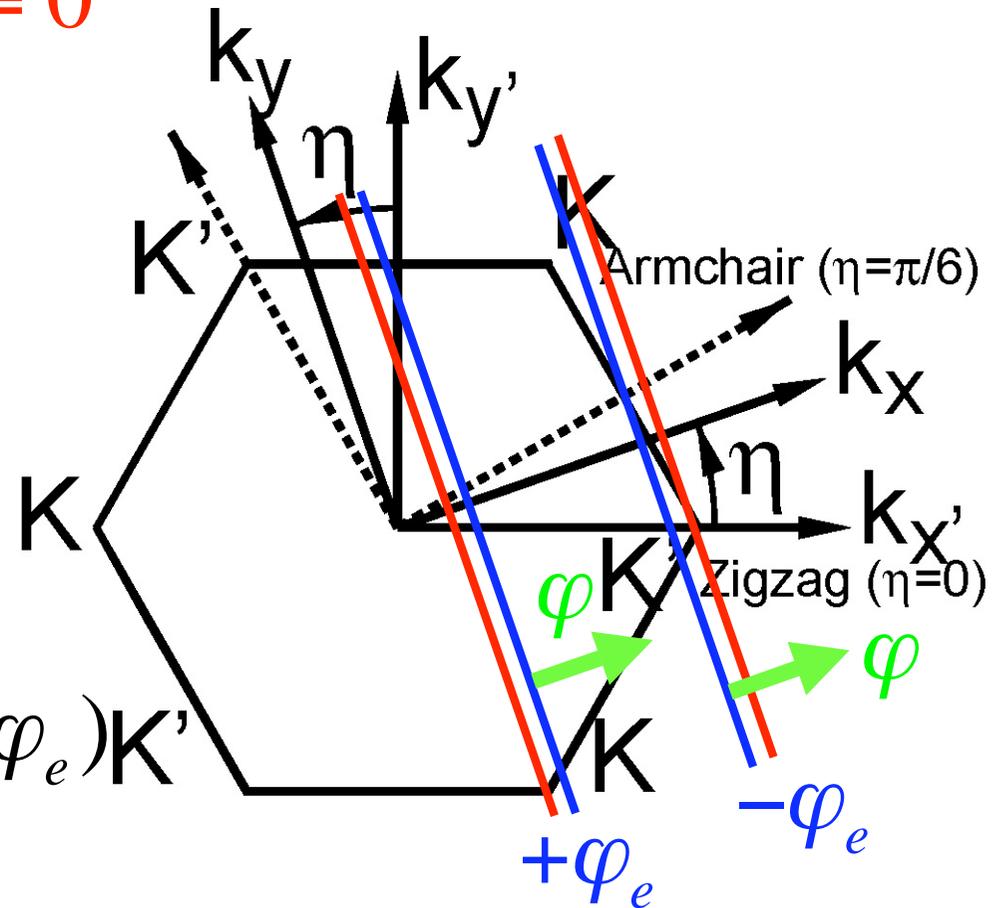
metal: $n = \varphi = \varphi_e = \kappa = 0$

Effective flux for strain, curvature and stress

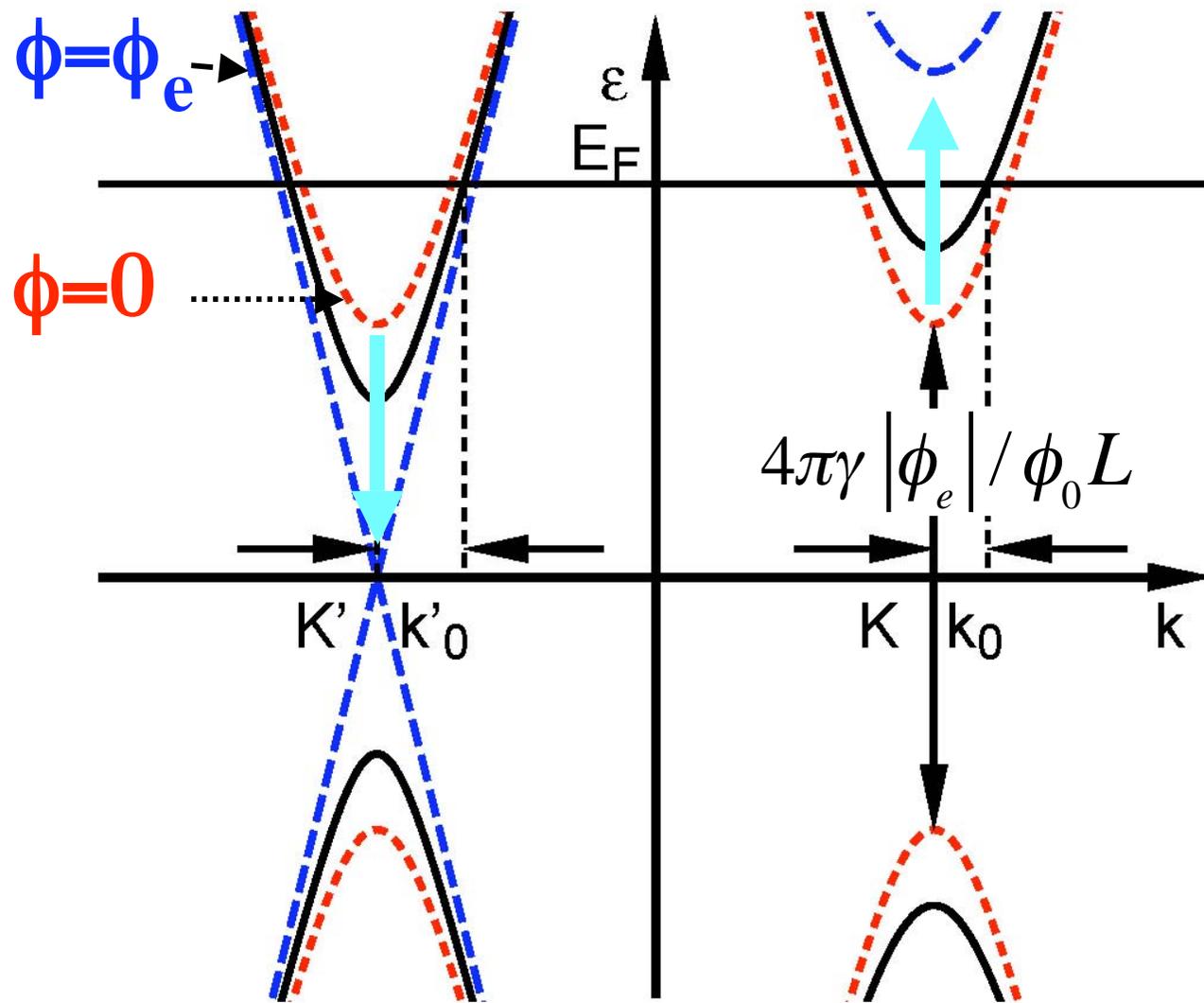
$$\varphi_e = \phi_e / \phi_0$$

$$K_{\varphi_e, \varphi}^{K} (n) = \frac{2\pi}{L} (n + \varphi + \varphi_e) K'$$

$$K_{\varphi_e, \varphi}^{K'} (n) = \frac{2\pi}{L} (n + \varphi - \varphi_e)$$

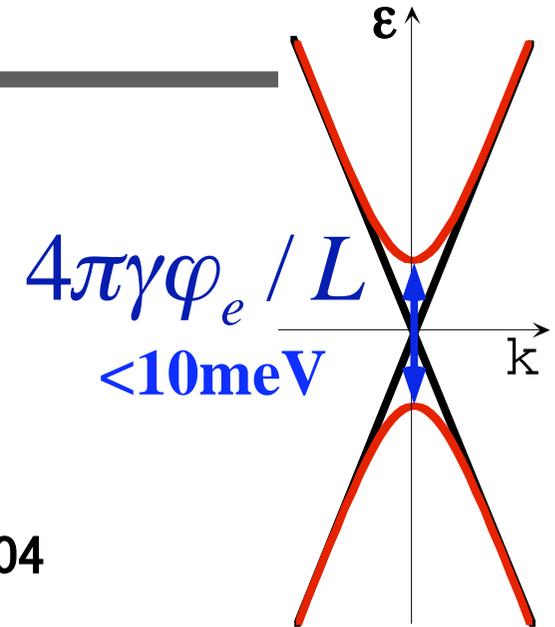


Schematic View of Bands



Method

- Effective-mass scheme
- Boltzmann Conductivity
- Effective Potential
 - Impurity: T. Ando and TN, JPSJ 67 (1998) 1704
 - Phonon: T. Ando and H. Suzuura, JPSJ 71 (2002) 2753
- Strain, curvature and stress effects

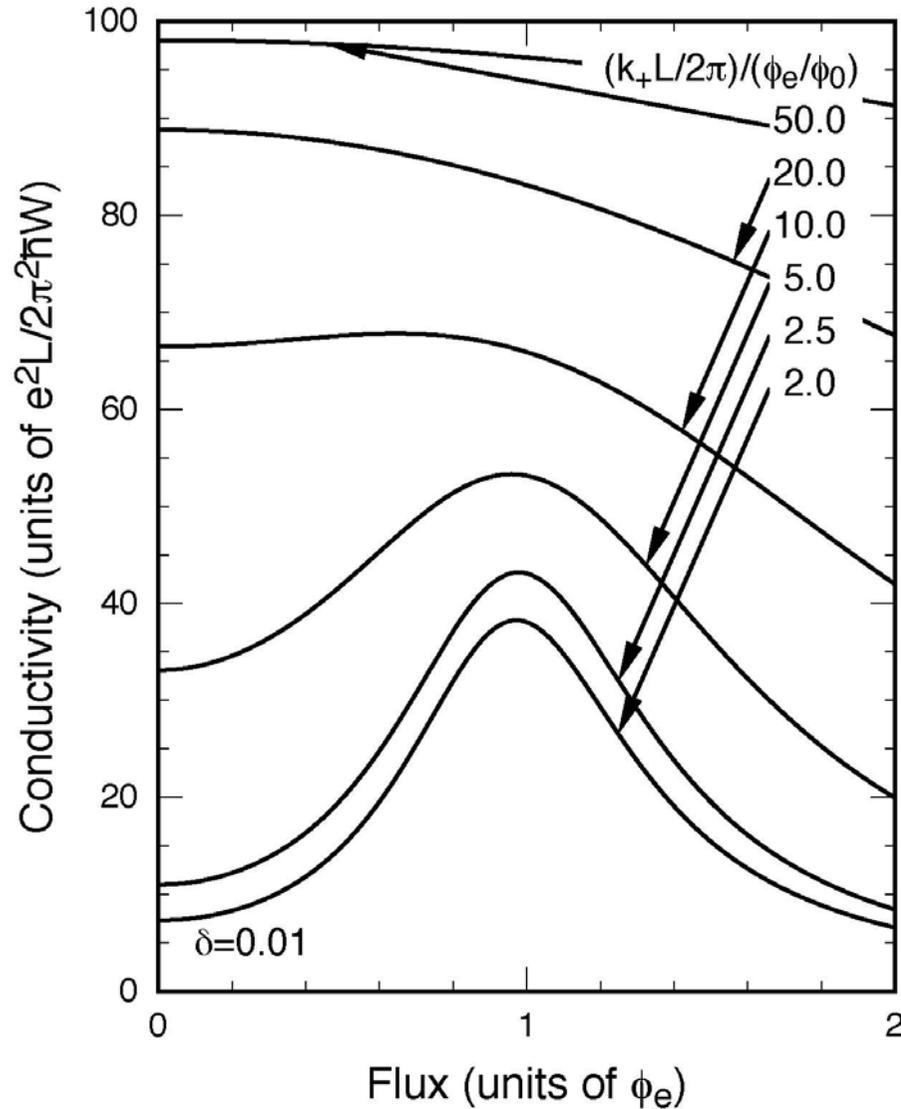


$$\varphi_e = \phi_e / \phi_0$$

$$K_{\varphi_e, \varphi}^{\text{K}}(n) = \frac{2\pi}{L} (n + \varphi + \varphi_e)$$

$$K_{\varphi_e, \varphi}^{\text{K}'}(n) = \frac{2\pi}{L} (n + \varphi - \varphi_e)$$

Nanotubes with small gap



➤ **Peak in Conductivity**

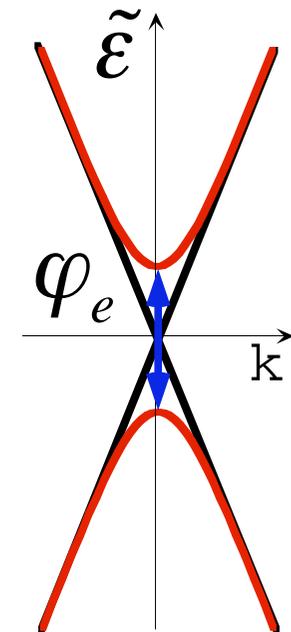
$$\sqrt{\delta / (1 - \delta)} (Lk_+ / 2\pi) < |\varphi_e|$$

➤ **k_+ : Charge Density**

➤ **δ : ratio of short-range potential**

➤ **In available magnetic field**

~10T



Boltzmann Conductivity

$$\sigma(\varphi) = \frac{e^2}{\pi \hbar} (\Lambda^K + \Lambda^{K'})$$

$$\frac{1}{\Lambda^{K'}} = \frac{1}{\Lambda_L^{K'}} + \frac{1}{\Lambda_S^{K'}}$$

$$\phi = \phi_e$$

$$K_{\varphi + \varphi_e} = \frac{2\pi}{L} (\varphi + \varphi_e)$$

$$\frac{1}{\Lambda_L^{K'}} = \frac{2\pi W (1 - \delta)}{L} \frac{K_{\varphi - \varphi_e}^2}{k_0'^2}$$

➤ k_0 : Charge Density

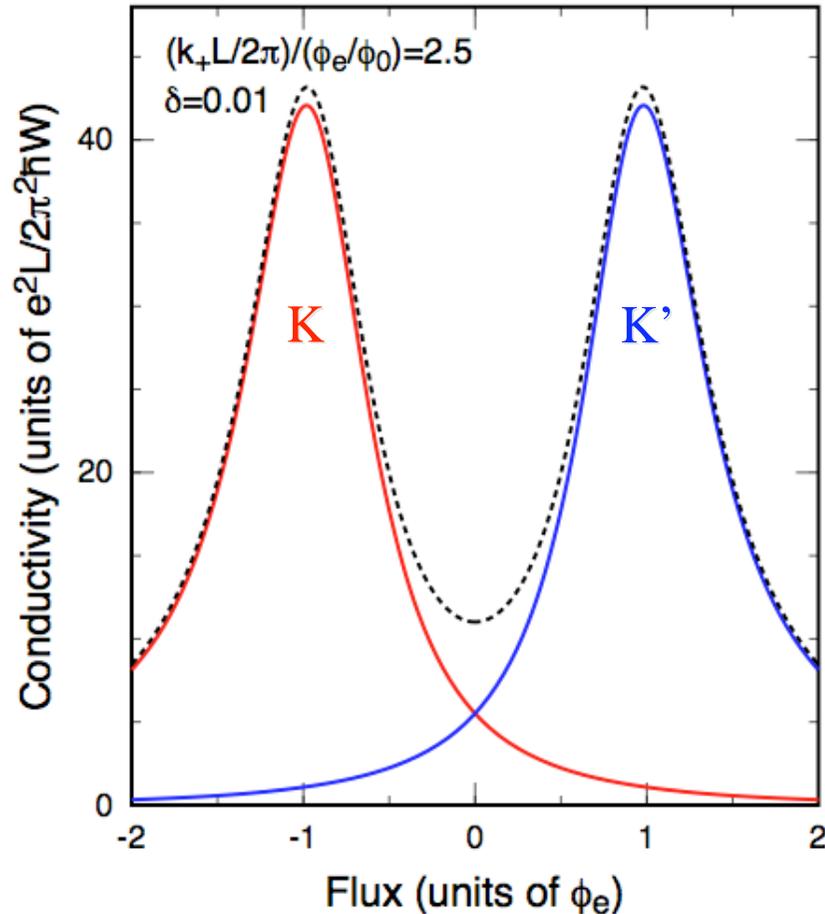
$$\frac{1}{\Lambda_S^{K'}} = \frac{2\pi W \delta}{L} \sqrt{1 + \frac{K_{\varphi - \varphi_e}^2}{k_0'^2}}$$

➤ δ : ratio of short-range

➤ W : Total scattering strength

$$\times \left[\sqrt{1 + \frac{K_{\varphi + \varphi_e}^2}{k_0^2}} + \sqrt{1 + \frac{K_{\varphi - \varphi_e}^2}{k_0'^2}} \right],$$

Peak in Conductivity



Lorentzian-like peak

$$\frac{1}{\Lambda^{K'}} = \frac{2\pi W(1-\delta)}{L} \left(\frac{2\pi}{Lk'_0} \right)^2 \left[(\varphi - \varphi_e)^2 + \Delta\varphi^2 \right],$$

$$\Delta\varphi = \sqrt{\frac{\delta}{1-\delta} \frac{Lk'_0}{2\pi}} \sqrt{1 + \sqrt{1 + 4\varphi_e^2 \left(\frac{2\pi}{Lk'_0} \right)^2}}$$

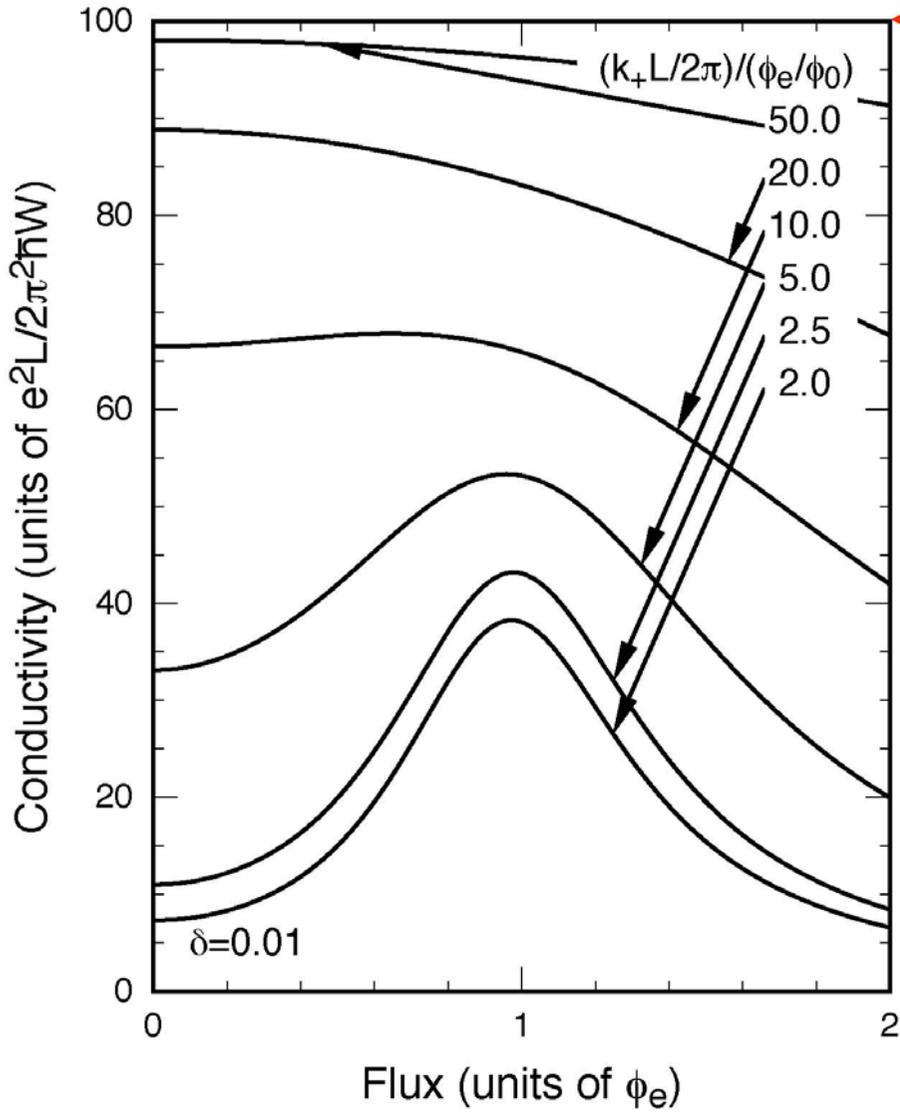
Condition to see the peak:

$$\sqrt{\delta / (1 - \delta)} (Lk_+ / 2\pi) < |\varphi_e|$$

$$k_+ = (k_0 + k'_0) / 2 \approx k'_0 \quad \text{for large density}$$

$$\sigma(\varphi) = \frac{e^2}{\pi \hbar} (\Lambda^K + \Lambda^{K'})$$

Large density and Scale



$$\sigma(\varepsilon) = \frac{e^2 L}{\pi^2 \hbar W} \frac{1}{2\delta} \quad \text{Gap-less}$$

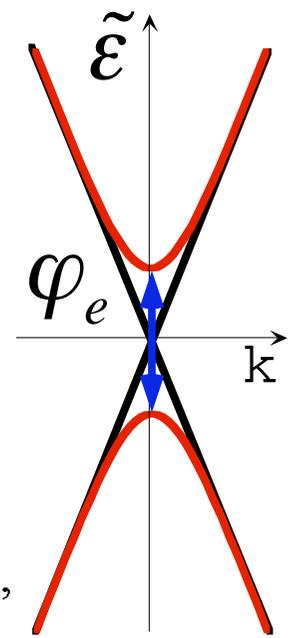
$$\frac{\kappa_{\varphi-\varphi_e}}{k_0'} = \left(\frac{\varphi_e}{\varphi} + 1 \right) / \left(\frac{Lk_0'}{2\pi} \frac{1}{\varphi_e} \right)$$

$$\frac{1}{\Lambda^{K'}} = \frac{1}{\Lambda_L^{K'}} + \frac{1}{\Lambda_S^{K'}}$$

$$\frac{1}{\Lambda_L^{K'}} = \frac{2\pi W(1-\delta)}{L} \frac{\kappa_{\varphi-\varphi_e}^2}{k_0'^2}$$

$$\frac{1}{\Lambda_S^{K'}} = \frac{2\pi W\delta}{L} \sqrt{1 + \frac{\kappa_{\varphi-\varphi_e}^2}{k_0'^2}}$$

$$\times \left[\sqrt{1 + \frac{\kappa_{\varphi+\varphi_e}^2}{k_0^2}} + \sqrt{1 + \frac{\kappa_{\varphi-\varphi_e}^2}{k_0'^2}} \right]$$

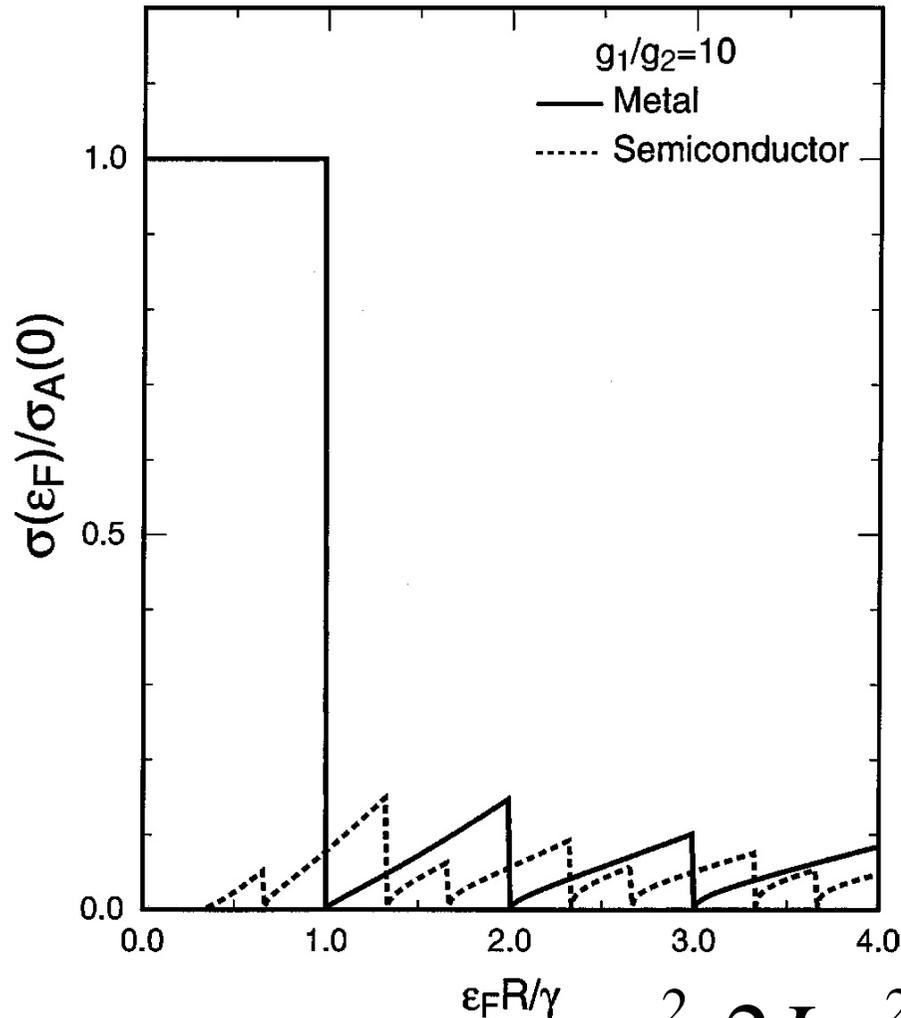


$$\sqrt{\delta / (1 - \delta)} (Lk_+ / 2\pi) < |\varphi_e|$$

Electron–Phonon Interaction

- **Suzuura and Ando, PRB 65 (2002) 235412**
- **Effective–Mass Theory**
- **Continuum model for acoustic phonons**
- **Elastic scattering approximation**
- **(High temperature approximation)**
- **Boltzmann Conductivity**
Relaxation time approximation
- **C. L. Kane and E. J. Mele, PRL 78 (1997) 1932**

Effective Potential



KA	KB	K'A	K'B
V_1	V_2	0	0
V_2^*	V_1	0	0
0	0	V_1	$-V_2^*$
0	0	$-V_2$	V_1

$$|V_1| \gg |V_2|$$

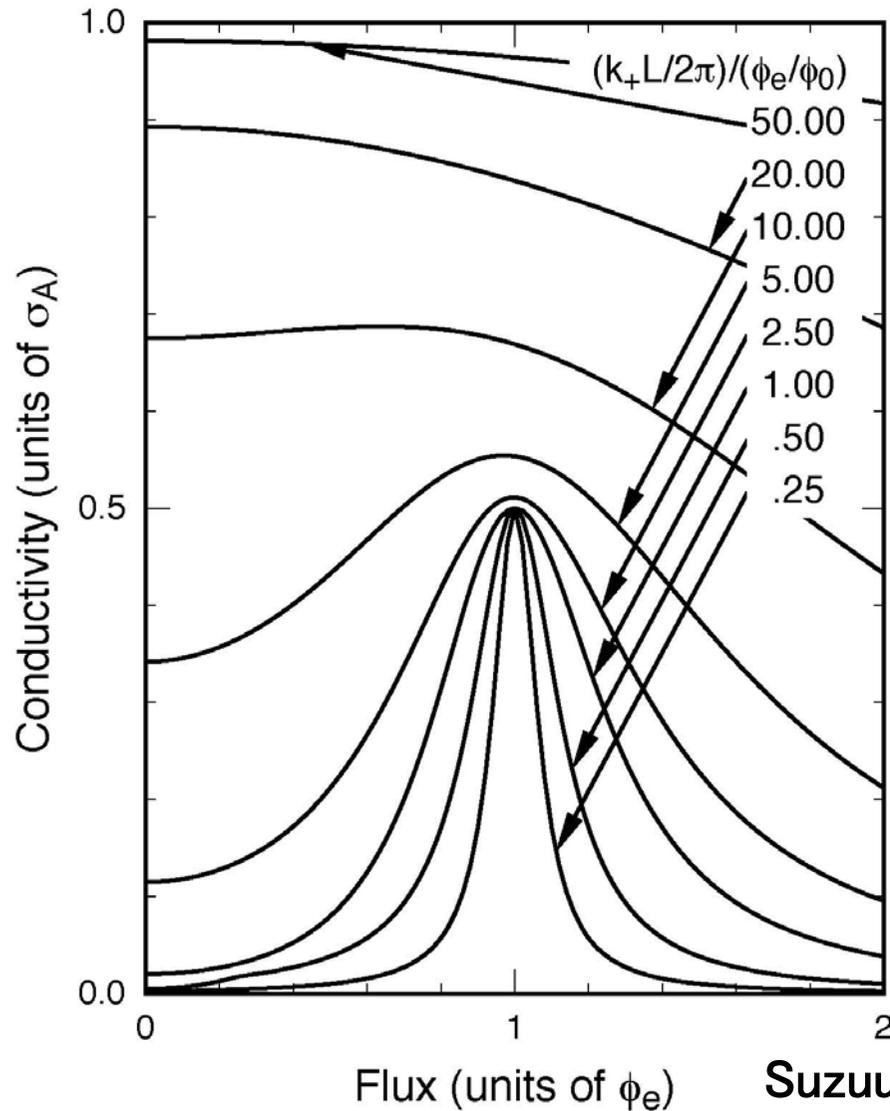
$$\sigma_A = \frac{e^2}{h} \frac{2L\gamma^2 \mu}{g_2^2 k_B T}$$

$\Lambda \sim 600L \sim 1\mu\text{m}$ at room temp.

(10,10) armchair CN

Ballistic conductor

$$\sigma_A = \frac{e^2}{h} \frac{2L\gamma^2\mu}{g_2^2 k_B T} \quad \text{Electron-Phonon}$$



➤ **Similar peak**

$$|V_1| \gg |V_2|$$

➤ **Effective potential**

KA	KB	K'A	K'B
V_1	V_2	0	0
V_2^*	V_1	0	0
0	0	V_1	$-V_2^*$
0	0	$-V_2$	V_1

Suzuura and Ando, PRB 65 (2002) 235412

Semiconducting Nanotubes

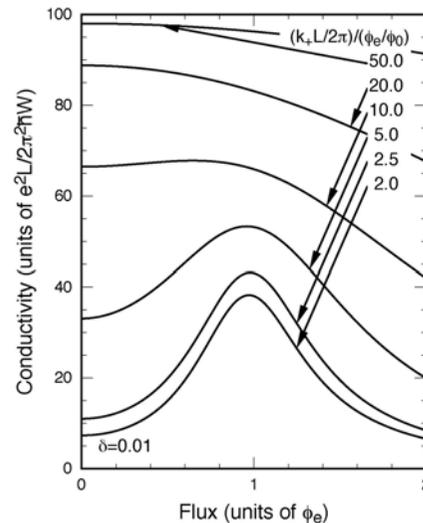
$\varphi_e \approx \pm 1/3$ too large to see the peak

$$\sigma(\varphi) = \sigma(0) + \frac{1}{2}\sigma''(0)\varphi^2 + \dots$$

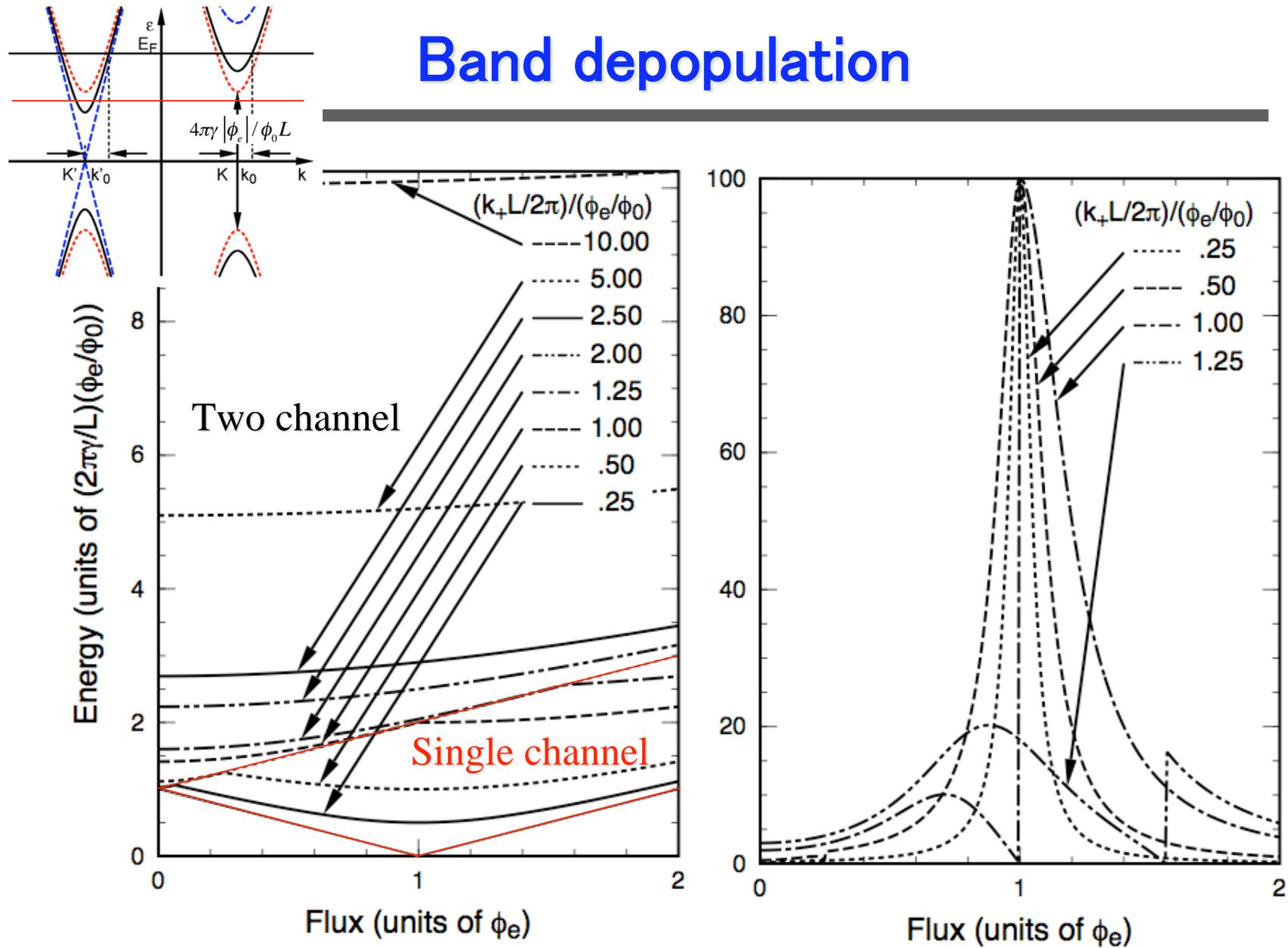
$$\sigma''(0) = \frac{4e^2}{\pi\hbar W} \frac{2\pi}{L} \frac{1-4\delta-\delta^2}{(1+\delta)^3} \frac{1}{k_+^2}$$

$\delta < \sqrt{5} - 2 = 0.236\dots$ Positive magnetoconductivity ($\sigma'' > 0$)

$\delta > \sqrt{5} - 2$ Negative magnetoconductivity ($\sigma'' < 0$)

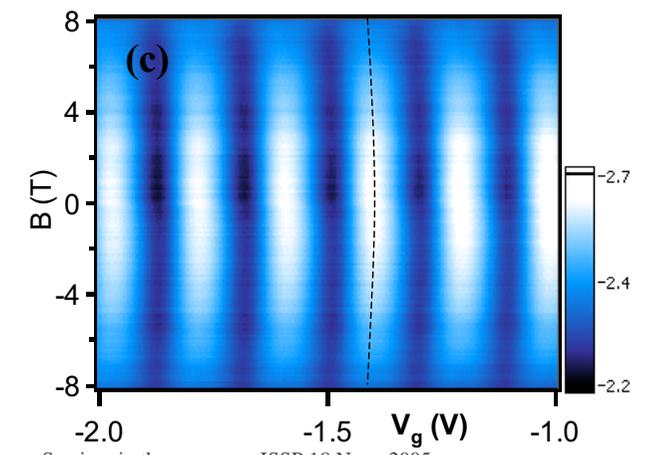
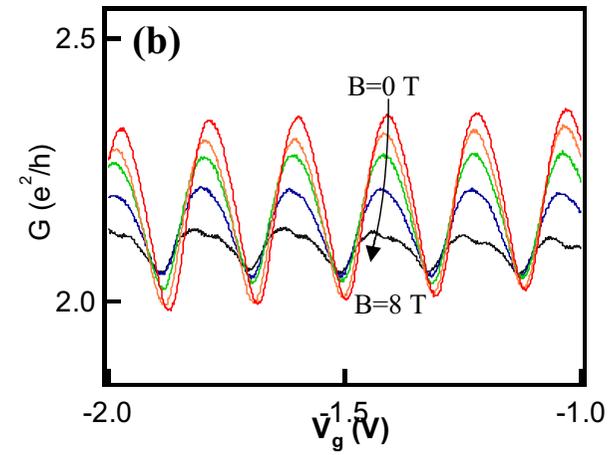
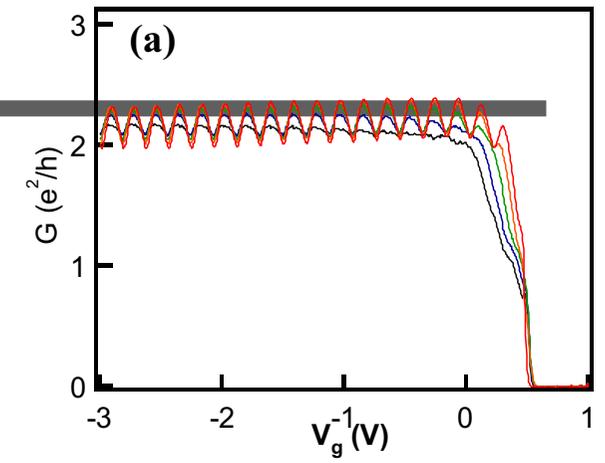
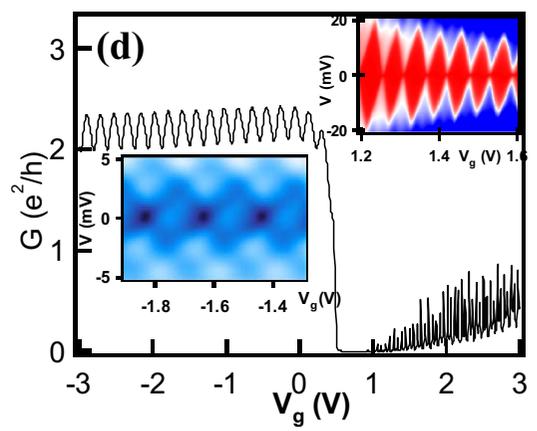
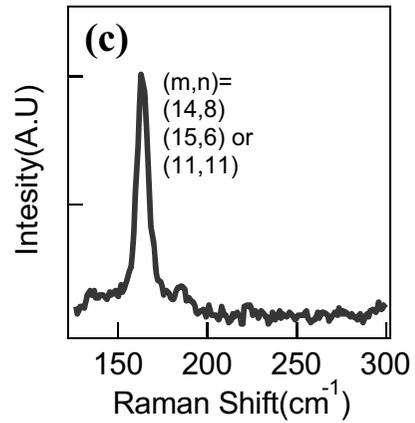
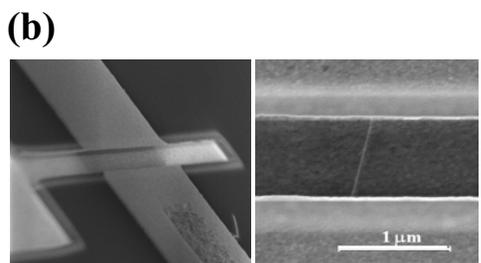
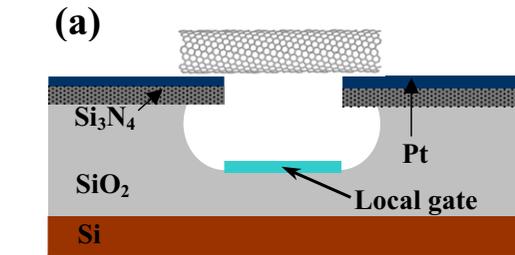


Band depopulation



AB effect

J. Cao *et al.* (Stanford)
PRL 93, 216803 (2004)



Conclusion

- Boltzmann conductivity
in carbon nanotubes
with magnetic flux in axis direction
- Impurity and electron-phonon scatterings
- Prediction of an experiment to know
 - strain, curvature and stress effects
 - ratio of short- and long- range potential
 - ratio of deformation potential and bond-length change
- TN and T. Ando, JPSJ 74 (2005) 3027